

N-channel 40 V, 1.7 mΩ logic level MOSFET in SOT78 1 February 2013

**Product data sheet** 

#### 1. **General description**

Logic level N-channel MOSFET in SOT78 using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

#### 2. **Features and benefits**

- High efficiency due to low switching & conduction losses •
- Robust construction for demanding applications
- Logic level gate

#### **Applications** 3.

- Battery-powered tools •
- Load switching
- Motor control
- Uninterruptible power supplies

#### 4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	150	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	349	W
Static charac	teristics	•					,
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11		-	1.4	1.7	mΩ
Dynamic cha	racteristics						
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V;		-	230	-	nC
Q <sub>GD</sub>	gate-drain charge	<u>Fig. 13; Fig. 14</u>		-	40.9	-	nC
Avalanche ru	ggedness	·			- 1	1	
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 150 \text{ A};  \text{V}_{sup} \leq 40  \text{V};  \text{R}_{GS} = 50  \Omega; \\ \text{V}_{GS} = 10  \text{V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{array}$		-	-	801.1	mJ

[1] Continuous current is limited by package.

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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain	$2 \rightarrow 0$	
3	S	source	TO-220AB (SOT78)	G G M M M M M M M M M M M M M M M M M M

# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN1R9-40PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN1R9-40PL	PSMN1R9-40PL

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

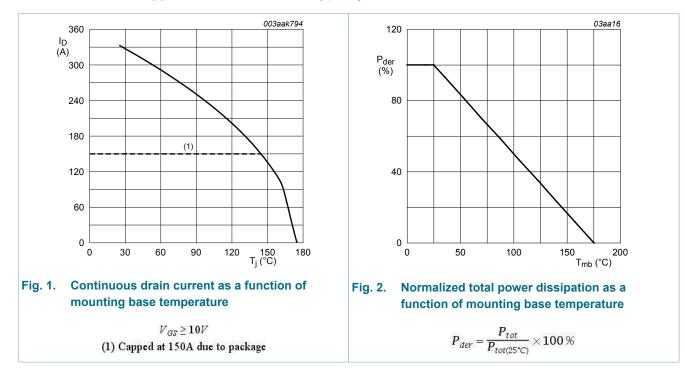
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	150	А
		T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	150	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	1332	А

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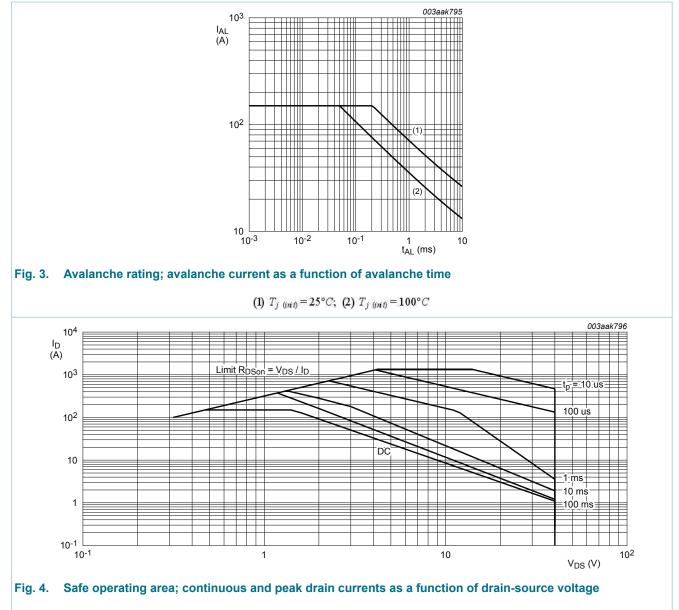
Symbol	Parameter	Conditions		Min	Мах	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	349	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain	n diode			_		
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	150	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1332	А
Avalanche r	uggedness			_		
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_D = 150 \; {\sf A};  {\sf V}_{sup} \le 40 \; {\sf V};  {\sf R}_{GS} = 50 \; \Omega; \\ & {\sf V}_{GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {\rm ^{\circ}C}; \; unclamped; \\ & {\sf Fig. \; 3} \end{split}$		-	801.1	mJ



[1] Continuous current is limited by package.

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 $T_{mb} = 25^{\circ}C; \ I_{DM}$  is a single pulse

## 9. Thermal characteristics

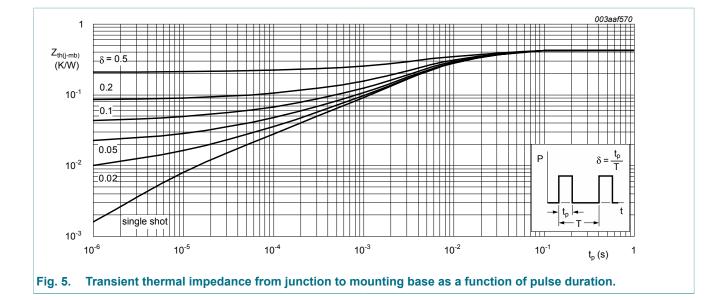
Table 6. The	Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	0.35	0.43	K/W	
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in still air		-	60	-	K/W	

#### Table 6. Thermal characteristic

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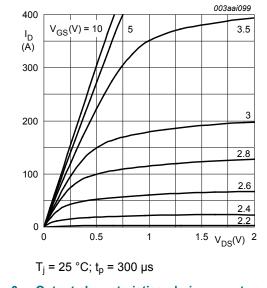


## **10. Characteristics**

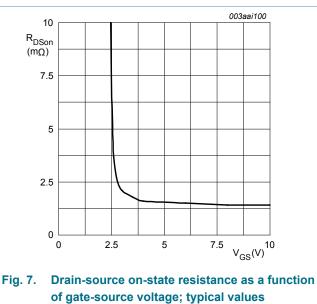
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·	I			_
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	36	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V	
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V	
I <sub>DSS</sub>		$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.13	1	μA
		$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	1.4	1.7	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	1.65	1.94	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	3.15	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	0.38	0.76	1.52	Ω

#### N-channel 40 V, 1.7 mΩ logic level MOSFET in SOT78

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics	· · · · · · · · · · · · · · · · · · ·				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 5 V; <u>Fig. 13</u> ; Fig. 14	-	120	-	nC
		$I_D$ = 25 A; $V_{DS}$ = 32 V; $V_{GS}$ = 10 V;	-	230	-	nC
Q <sub>GS</sub>	gate-source charge	<u>Fig. 13; Fig. 14</u>	-	26.9	-	nC
Q <sub>GD</sub>	gate-drain charge		-	40.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	13200	-	pF
C <sub>oss</sub>	output capacitance		-	1530	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	740	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 5 V;	-	95	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	118	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	195	-	ns
t <sub>f</sub>	fall time		-	119	-	ns
Source-dra	in diode		I			
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	57	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	97	-	nC







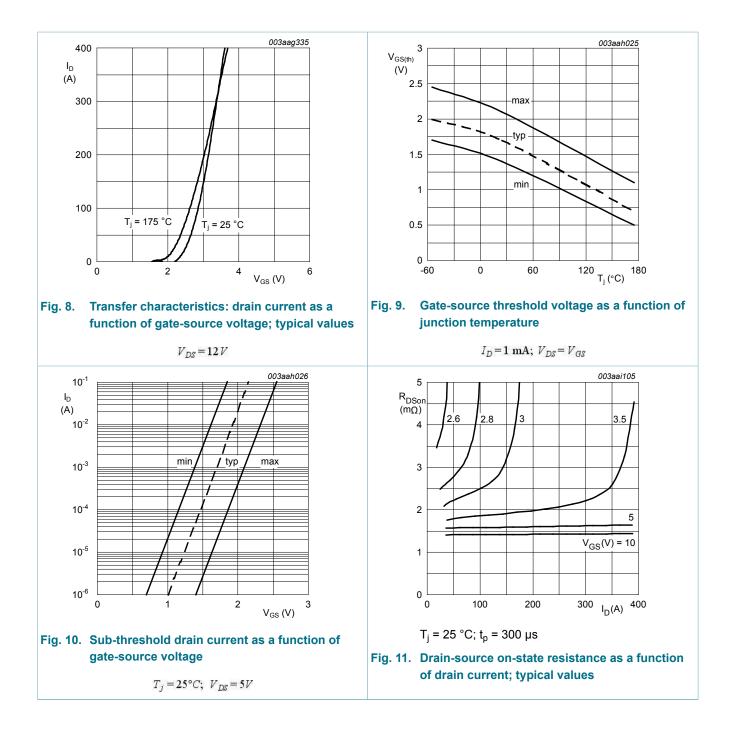
te-source voltage; typical value

 $T_j = 25^{\circ}C; \ I_D = 25A$ 

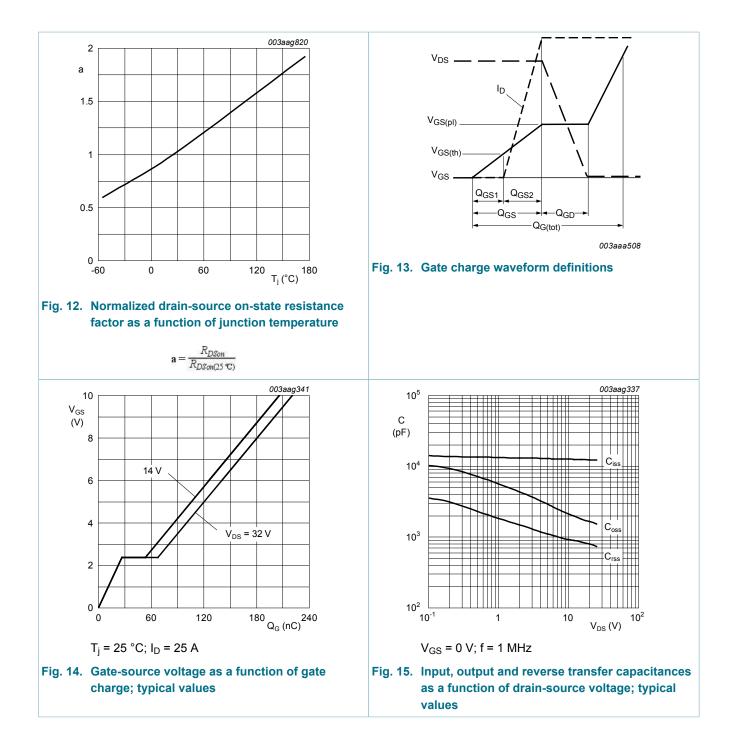
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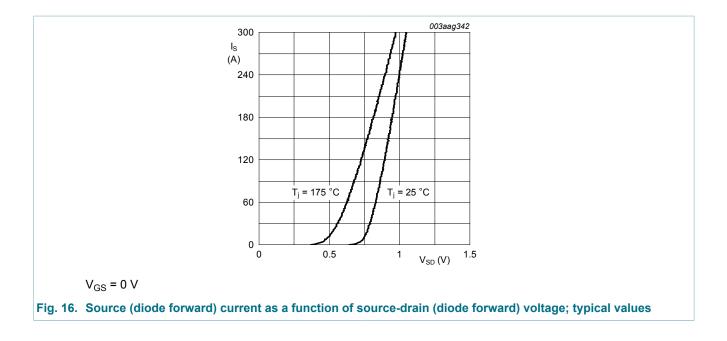


#### N-channel 40 V, 1.7 mΩ logic level MOSFET in SOT78



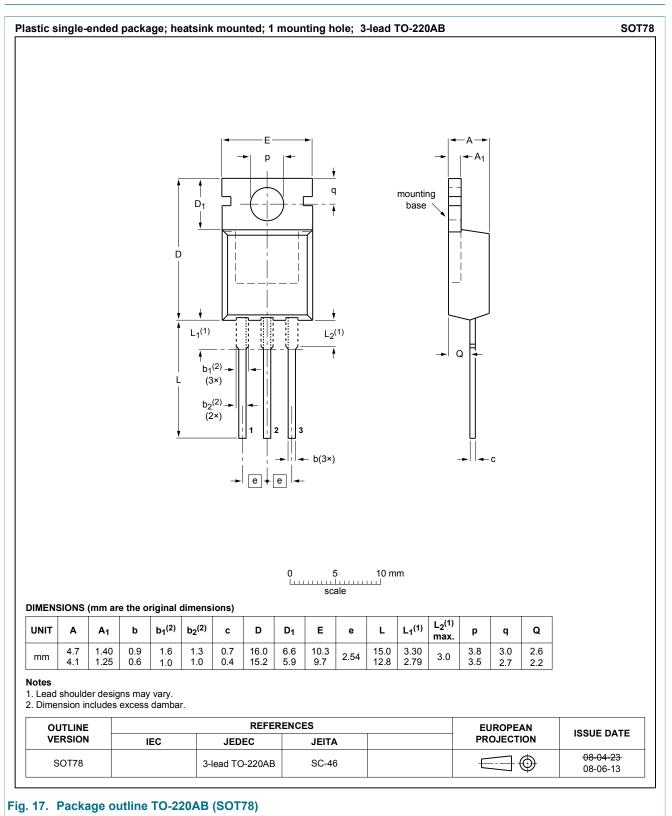
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#### N-channel 40 V, 1.7 mΩ logic level MOSFET in SOT78



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## 11. Package outline



#### PSMN1R9-40PL

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